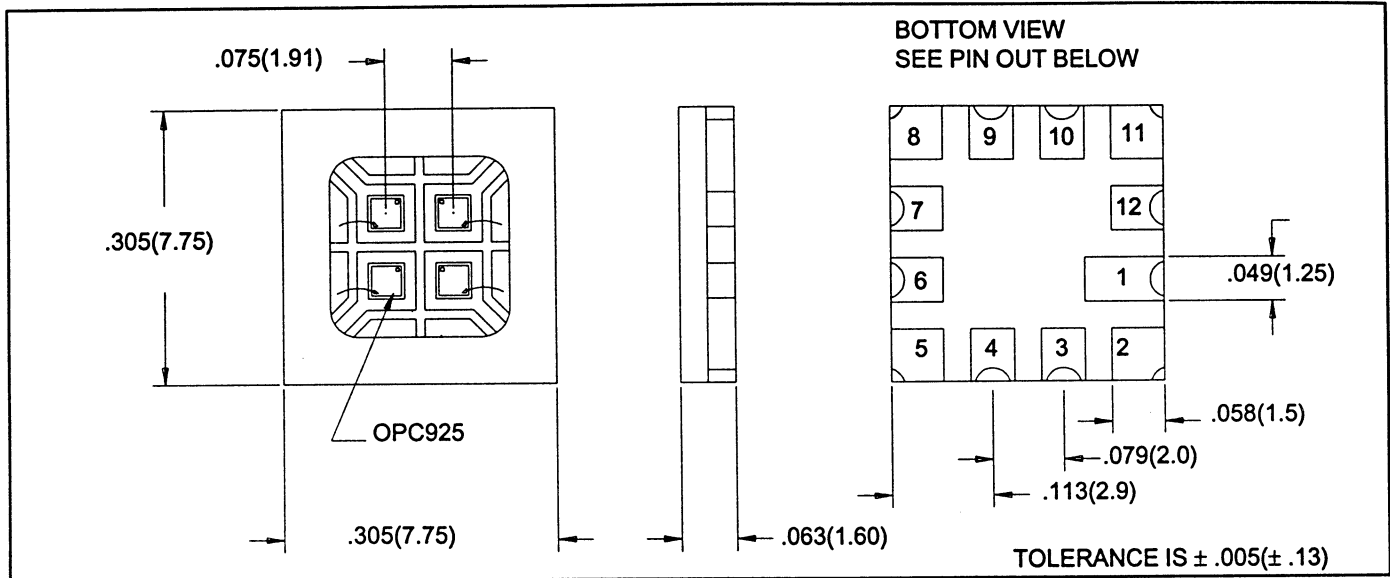


Surface Mount Quad Photodiode Type OPR5925



Features

- Surface Mountable
- Separate Cathode Connections
- High Temperature Operation

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Storage and Operating Temperature	-55°C to $+125^\circ\text{C}$
Reverse Breakdown Voltage	35 V Min.
Solder Temperature (Vapor Phase Reflow for 30 sec.)	235°C

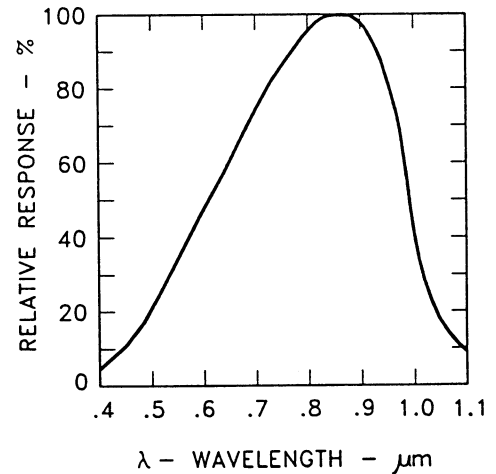
Description

This compact polyimide chip carrier contains four silicon photodiodes in a quad arrangement with each anode and cathode bonded out separately. The internal isolation enables external connection in any desired configuration to match the sensing circuit requirements. The custom opaque package material shields the photodiodes from stray light and can withstand multiple exposures to the most demanding soldering conditions. The wrap around solder pads are gold plated for exceptional storage and wetting characteristics.

PIN OUT:

- | | |
|---------|------------|
| PIN #1. | ANODE #1 |
| 2. | CATHODE #1 |
| 3. | N/C |
| 4. | N/C |
| 5. | CATHODE #2 |
| 6. | ANODE #2 |
| 7. | ANODE #3 |
| 8. | CATHODE #3 |
| 9. | N/C |
| 10. | N/C |
| 11. | CATHODE #4 |
| 12. | ANODE #4 |

SPECTRAL RESPONSIVITY



Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITION
R_λ	Responsivity	.45			A/W	$\Phi_e = 10 \mu\text{W}$, $\lambda = 890 \text{ nm}$, $V_R = 0 \text{ V}$
$V_{(BR)R}$	Reverse Breakdown Voltage	35			V	$I_R = 100 \mu\text{A}$
I_D	Reverse Dark Current			30	nA	$V_R = 10 \text{ V}$
C_T	Capacitance		10		pf	$V_R = 10 \text{ V}$
L x W	Active Area (per diode)		0.64		mm^2	(0.8 mm x 0.8 mm)

HYBRID ASSEMBLIES